

EAST - [lg.wsp:1]

File View Edit Tools Window Help

Search:

12: (16657) 1 and gate.clm.
 13: (6379) 2 and flash
 14: (5286) 3 and (floating or control).clm.
 15: (4423) 4 and (tunnel or oxide)
 16: (2494) 5 and dielectric
 17: (1363) 6 and oxidation
 18: (13) 7 and (dry adj oxidis5)
 19: (7) 8 and ((sidewall\$1) or (side adj wall\$1))
 20: (0) 5 and CS1HS1Cl\$1
 21: (20) 5 and (dry adj oxidis4)
 22: (13) 11 and (sidewall or (side adj wall))

Search:

DBs: USPAT-US-PCPUS Plurals Highlight all hit terms initially
 Default operator: OR AND

11 and (sidewall or (side adj wall))

BR2 term BR4 term Image Text HTML

V	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	S	Imat	
1	<input checked="" type="checkbox"/>	US 20040004894	20040108	48	Semiconductor integrated circuit and nonvolatile memo	365/222			Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 2004				
2	<input checked="" type="checkbox"/>	US 20020106859	20020808		Method of fabricating nonvolatile semiconductor me	438/264			Odake, Yoshinori et al.	<input checked="" type="checkbox"/>					
3	<input checked="" type="checkbox"/>	US 20020079533	20020627	12	Semiconductor memory device and its manufacture	257/315	257/E29.129; 257/E29.306		Horiguchi, Naoto et al.	<input checked="" type="checkbox"/>	US 2002				
4	<input checked="" type="checkbox"/>	US 20020019100	20020214	53	METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIR	438/275	257/E21.625; 257/E21.632		SHUKURI, SHOJI et al.	<input checked="" type="checkbox"/>	US 2002				
5	<input checked="" type="checkbox"/>	US 20020014641	20020207	53	Semiconductor integrated circuit device and having de	257/275	257/E21.625; 257/E21.632		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 2002				
6	<input checked="" type="checkbox"/>	US 20020009851	20020124	52	Method for manufacturing semiconductor integrated cir	438/257	257/E21.625; 257/E21.632		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 2002				
7	<input checked="" type="checkbox"/>	US 20020006054	20020117	51	Semiconductor integrated circuit and nonvolatile memo	365/145			Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 2002				
8	<input checked="" type="checkbox"/>	US 6614684 B1	20030902	48	Semiconductor integrated circuit and nonvolatile memo	365/185.05	257/318; 365/185.09		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 0				
9	<input checked="" type="checkbox"/>	US 6559012 B2	20030506	51	Method for manufacturing semiconductor integrated cir	438/275	257/E21.625; 257/E21.632;		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 0				
10	<input checked="" type="checkbox"/>	US 6528839 B2	20030304	50	Semiconductor integrated circuit and nonvolatile memo	257/314	257/319; 257/316		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	US 0				
11	<input checked="" type="checkbox"/>	US 6207991 B1	20010327	16	Integrated non-volatile and CMOS memories having substan	257/326	257/E21.635; 257/E21.639;		Rahim, Irfan	<input checked="" type="checkbox"/>	US 0				
12	<input checked="" type="checkbox"/>	US 6124157 A	20000926	16	Integrated non-volatile and random access memory and met	438/201	257/E21.552; 257/E21.689;		Rahim, Irfan	<input checked="" type="checkbox"/>	US 0				
13	<input checked="" type="checkbox"/>	US 5976927 A	19991102	10	Two mask method for reducing field oxide encroachment in	438/239	257/E21.552; 257/E21.646;		Hsieh, Chia-Ta et al.	<input checked="" type="checkbox"/>	US 0				

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